



## LED405-66-60

- Violet multi-chip high power LED Array
- 405 nm, 600 mW
- InGaN structure
- UV-resistant clear silicone resin
- TO-66 package



### Description

**LED405-66-60** is an **InGaN** based multi-chip UV LED array, typically emitting at 405nm with a typical output power of 600 mW. It comprises 60pcs of LED chips, arranged in combined parallel and serial connection, in a TO-66 metal package with hermetically sealed **UV-resistant silicone resin**.

### Maximum Rating ( $T_{CASE} = 25^{\circ}C$ )

Parameter	Symbol	Values		Unit
		Min.	Max.	
Power Dissipation, DC	$P_D$		12	W
Forward Current	$I_F$		600	mA
Reverse Voltage	$V_R$		25	V
Thermal Resistance	$R_{thja}$		330	K/W
Junction Temperature	$T_J$		120	$^{\circ}C$
Operating Temperature	$T_{OPR}$	- 40	+ 85	$^{\circ}C$
Storage Temperature	$T_{STG}$	- 40	+ 100	$^{\circ}C$
Soldering Temperature (max 3s)	$T_{SOL}$		+ 265	$^{\circ}C$



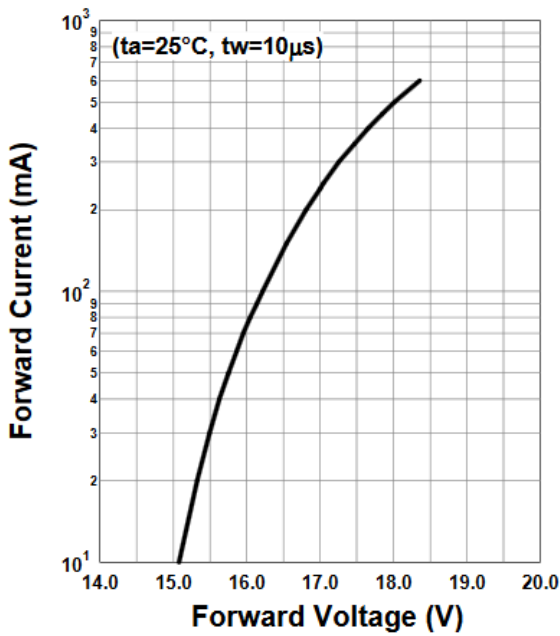
### Electro-Optical Characteristics ( $T_{CASE} = 25^{\circ}C, I_F = 240 mA$ )

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Peak Wavelength <sup>*1</sup>	$\lambda_P$	400		410	nm
Spectral Width (FWHM)	$\Delta\lambda$		19		nm
Forward Voltage	$V_F$		17	20	V
Radiated Power	$P_O$		600		mW
Viewing Half Angle	$\Theta_{1/2}$		$\pm 62$		deg.
Rise/Fall Time	$t_r$		10/15		ns

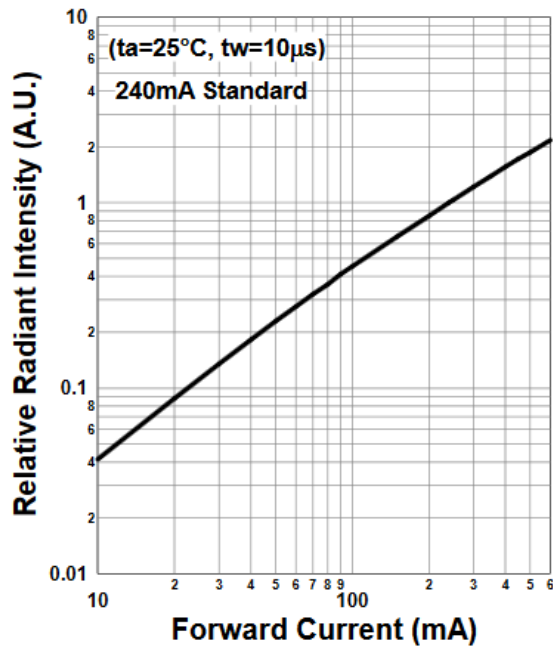


## Performance Characteristics

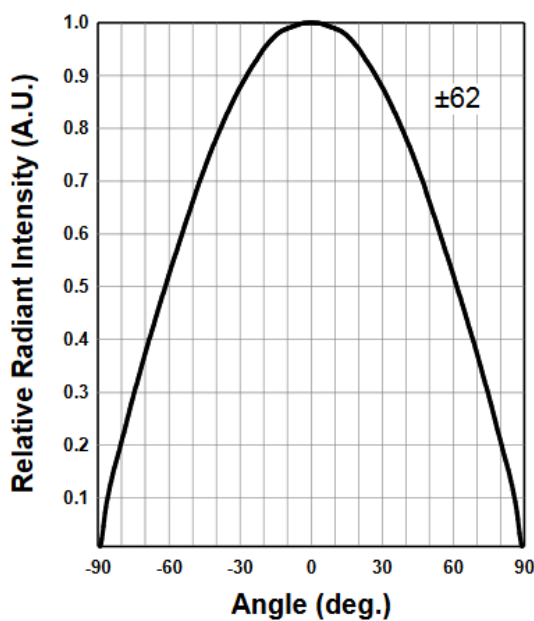
### Forward Current vs. Forward Voltage



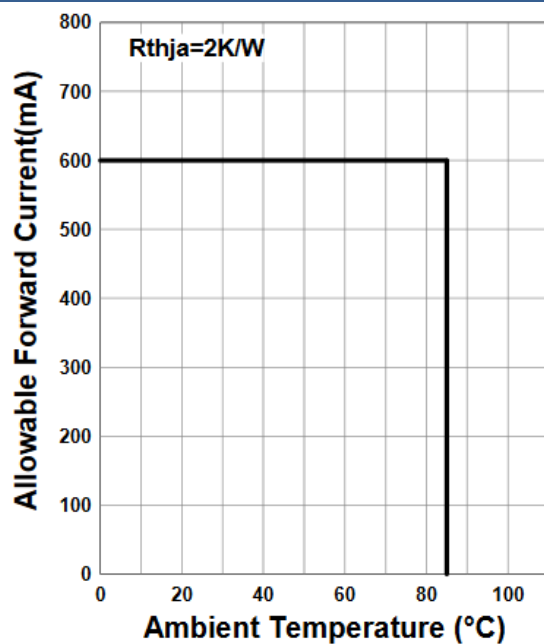
### Relative Radiant Intensity vs. Forward Current



### Radiation Characteristics



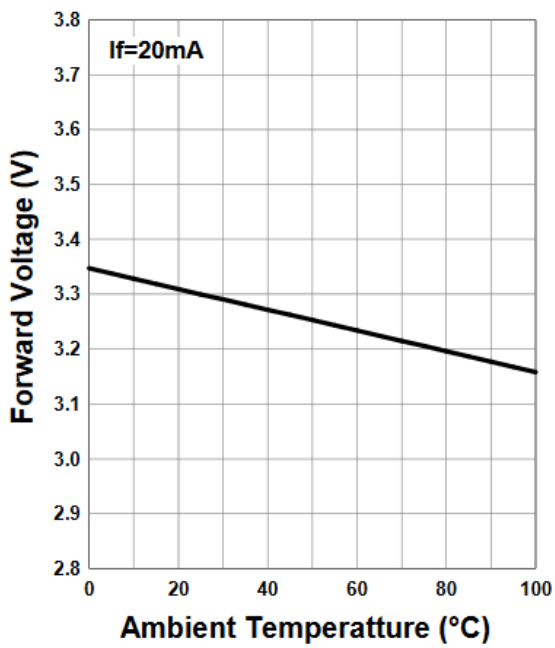
### Allowable Forward Current vs. Ambient Temp.



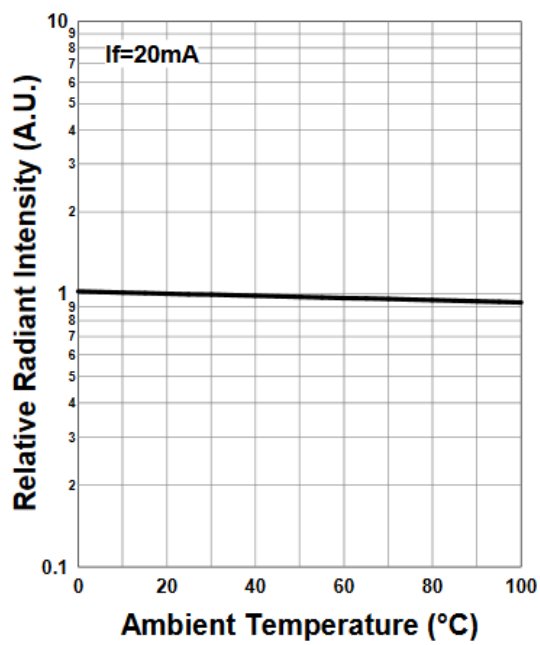


## Performance Characteristics

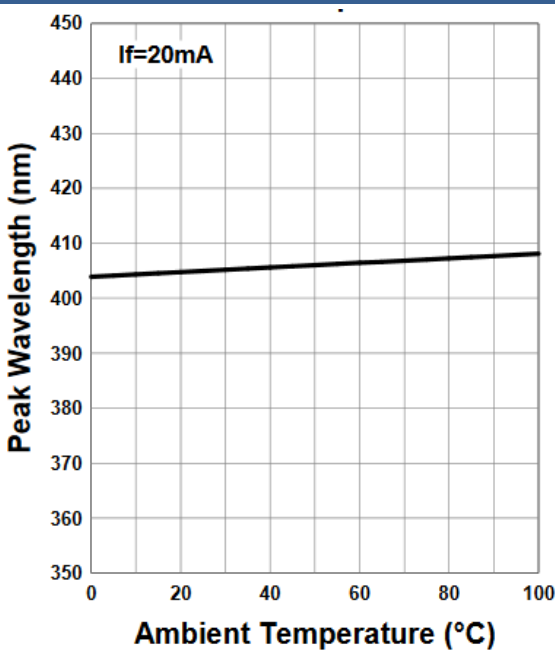
### Forward Voltage vs. Ambient Temperature



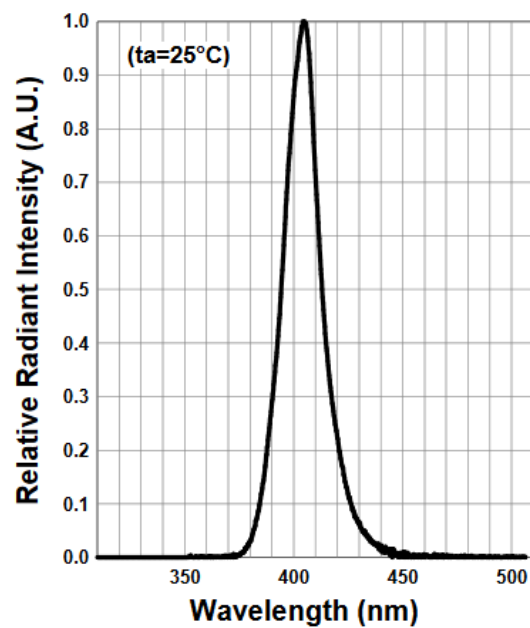
### Relative Radiant Intensity vs. Ambient Temp.



### Peak Wavelength vs. Ambient Temperature

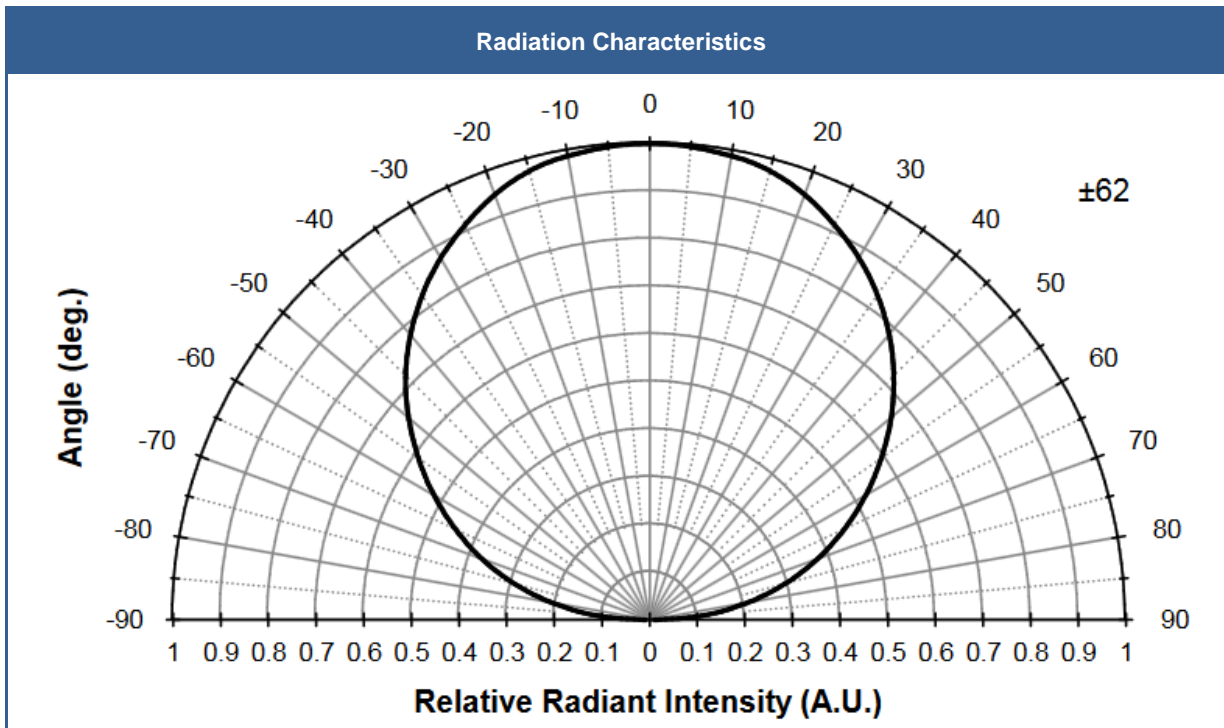


### Relative Spectral Emission

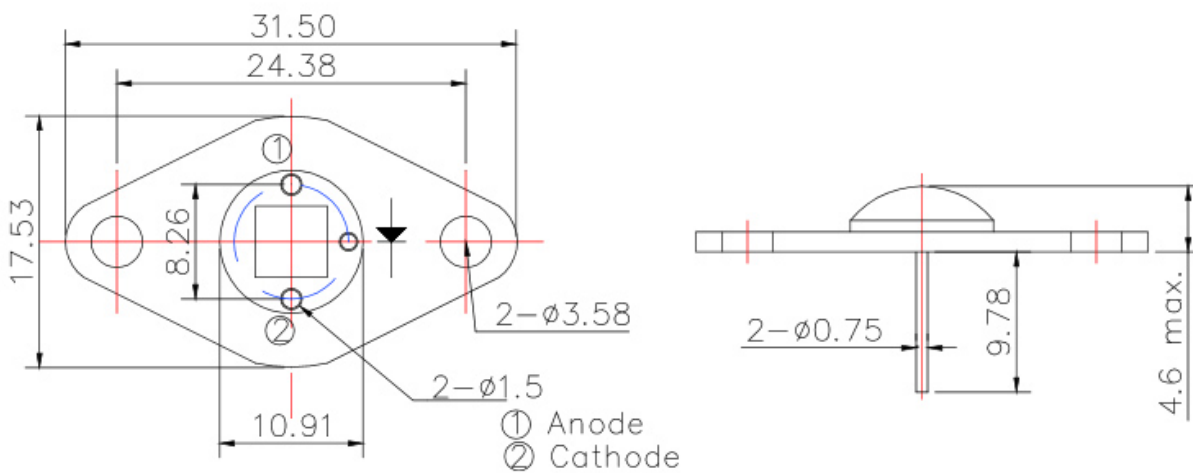




## Performance Characteristics



## Outline Dimensions



All dimensions in mm